

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

**(19) World Intellectual Property
Organization
International Bureau**



(43) International Publication Date
30 September 2004 (30.09.2004)

PCT

(10) International Publication Number
WO 2004/084307 A1

(51) International Patent Classification⁷: H01L 27/11,
G11C 11/412, H01L 27/144

(81) Designated States (national): CN, JP, KR, US.

(21) International Application Number:
PCT/IB2003/001078

(84) Designated States (regional): European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR).

(22) International Filing Date: 21 March 2003 (21.03.2003)

(25) Filing Language: English

Published:
— *with international search report*

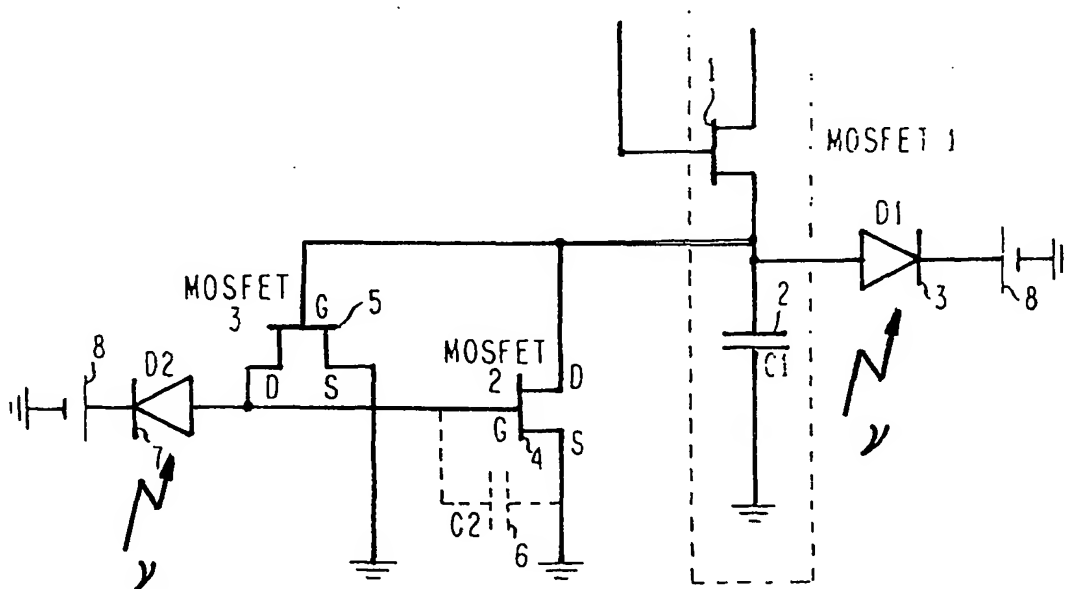
(26) **Publication Language:** English

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For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: SINGLE ENDED THREE TRANSISTOR QUASI-STATIC RAM CELL



(57) Abstract: A single ended three transistor quasi-static RAM cell comprises two cross coupled MOS transistors and one select MOS transistor connected to drain of one of the aforementioned MOS transistors wherein drains of both cross coupled MOS transistors are each connected to anode of one of two PN diodes functioning as constant current loads when exposed to continuous light from LED diode.

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